74ALVCH16501

18-bit universal bus transceiver; 3-state Rev. 5 — 10 July 2012

Product data sheet

General description 1.

The 74ALVCH16501 is an 18-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. Data flow in each direction is controlled by output enable (OEAB and OEBA), latch enable (LEAB and LEBA), and clock (CPAB and CPBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is HIGH. When LEAB is LOW, the A data is latched if CPAB is held at a HIGH or LOW logic level. If LEAB is LOW, the A-bus data is stored in the latch/flip-flop on the LOW-to HIGH transition of CPAB. When OEAB is HIGH, the outputs are active. When OEAB is LOW, the outputs are in the high-impedance state.

Data flow for B-to-A is similar to that of A-to-B but uses OEBA, LEBA and CPBA. The output enables are complimentary (OEAB is active HIGH, and OEBA is active LOW.

To ensure the high-impedance state during power-up or power-down, OEBA should be tied to V_{CC} through a pull-up resistor and OEAB should be tied to GND through a pull-down resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Features and benefits 2.

- Wide supply voltage range from 1.2 V to 3.6 V
- Complies with JEDEC standard JESD8-B
- CMOS low power consumption
- Direct interface with TTL levels
- Current drive ±24 mA at V_{CC} = 3.0 V
- Universal bus transceiver with D-type latches and D-type flip-flops capable of operating in transparent, latched or clocked mode
- All inputs have bus hold circuitry
- Output drive capability 50 Ω transmission lines at 85 °C
- 3-state non-inverting outputs for bus-oriented applications

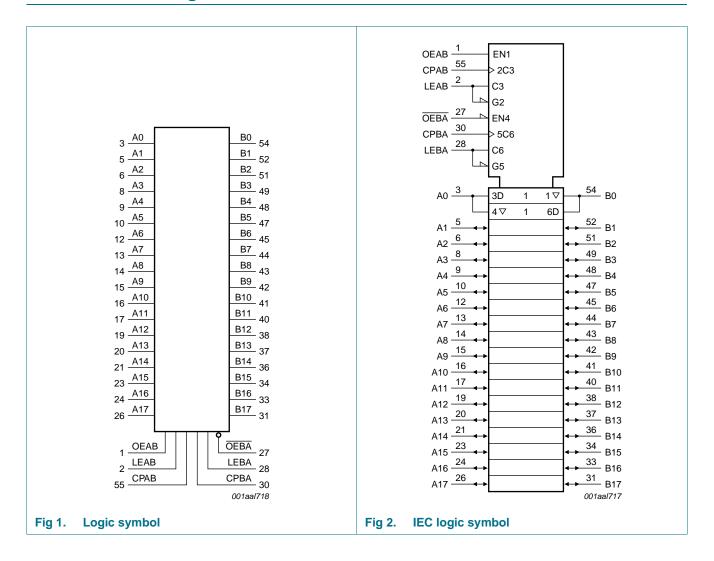


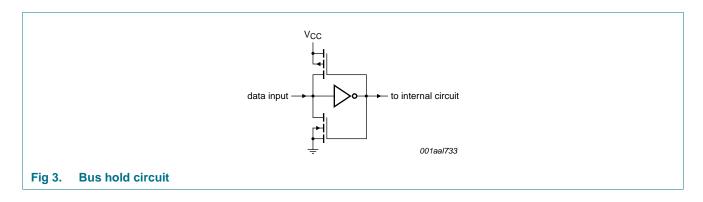
3. Ordering information

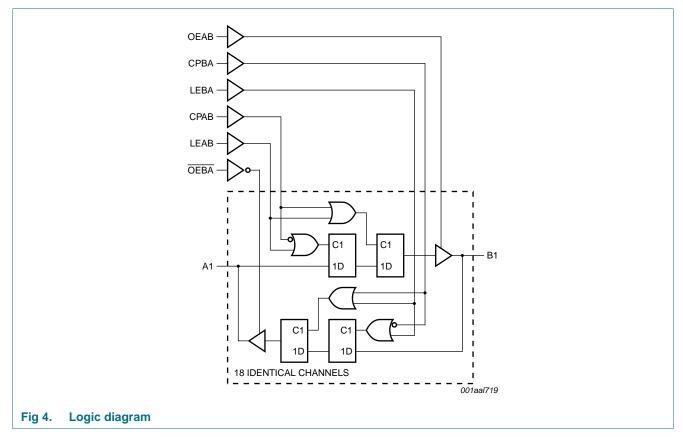
Table 1. Ordering information

Type number	nber Package								
	Temperature range	Name	Description	Version					
74ALVCH16501DGG	–40 °C to +85 °C	TSSOP56	plastic thin shrink small outline package; 56 leads; body width 6.1 mm	SOT364-1					
74ALVCH16501DL	–40 °C to +85 °C	SSOP56	plastic shrink small outline package; 56 leads; body width 7.5 mm	SOT371-1					

4. Functional diagram

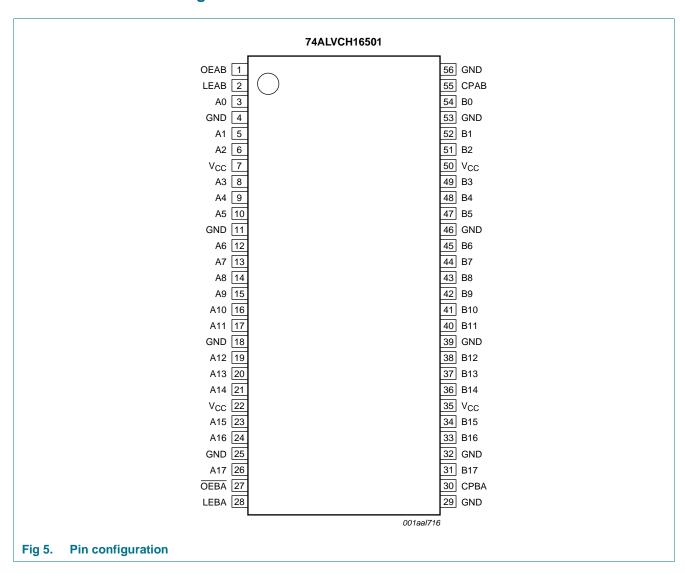






5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

	·	
Symbol	Pin	Description
OEAB	1	output enable A-to-B input
LEAB	2	latch enable A-to-B input
A0 to A17	3, 5, 6, 8, 9, 10, 12, 13, 14, 15, 16, 17, 19, 20, 21, 23, 24, 26	data inputs or outputs
GND	4, 11, 18, 25, 29, 32, 39, 46, 53, 56	ground (0 V)
V _{CC}	7, 22, 35, 50	positive supply voltage
OEBA	27	output enable B-to-A
LEBA	28	latch enable B-to-A

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Table 2. Pin description ...continued

Symbol	Pin	Description
СРВА	30	clock input B-to-A
B0 to B17	54, 52, 51, 49, 48, 47, 45, 44, 43, 42, 41, 40, 38, 37, 36, 34, 33, 31	data inputs or outputs
CPAB	55	clock input A-to-B

6. Functional description

6.1 Function table

Table 3. Function table[1]

Inputs				Output	Operating mode
OEAB	LEAB	СРАВ	An	Bn	
L	X	X	X	Z	disabled
Н	Н	X	Н	Н	transparent
Н	Н	X	L	L	
Н	\	X	h	Н	latch data and display
Н	\	X	I	L	
Н	L	↑	h	Н	clock data and display
Н	L	↑	I	L	
Н	L	H or L	X	Н	hold data and display
Н	L	H or L	Χ	L	_

^[1] A-to-B data flow is shown; B-to-A flow is similar but uses OEBA, LEBA and CPBA.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V_{I}	input voltage	control inputs	<u>[1]</u> –0.5	+4.6	V
		data inputs	<u>[1]</u> –0.5	$V_{CC} + 0.5$	V
I _{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0 V$	-	±50	mA
V_{O}	output voltage		<u>[1]</u> –0.5	$V_{CC} + 0.5$	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I _{CC}	supply current		-	100	mA

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H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the enable or clock transition;

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the enable or clock transition;

X = don't care;

Z = high-impedance OFF-state;

 $[\]downarrow$ = HIGH-to-LOW clock transition;

 $[\]uparrow$ = LOW-to-HIGH clock transition.

 Table 4.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
I_{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$			
		SSOP package	[2] -	850	mW
		TSSOP package	<u>[3]</u> _	600	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
V_{CC}	supply voltage	maximum speed performance								
		C _L = 30 pF	2.3	-	2.7	V				
		C _L = 50 pF	3.0	-	3.6	V				
		low-voltage applications	1.2	-	3.6	V				
VI	input voltage		0	-	V_{CC}	V				
Vo	output voltage		0	-	V_{CC}	V				
T _{amb}	ambient temperature	in free air	-40	-	+85	°C				
Δt/ΔV	input transition rise and fall	V _{CC} = 2.3 V to 3.0 V	0	-	20	ns/V				
	rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0	-	10	ns/V				

^[2] Above 55 °C the value of Ptot derates linearly with 11.3 mW/K.

^[3] Above 55 °C the value of Ptot derates linearly with 8 mW/K.

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
$T_{amb} = -4$	10 °C to +85 °C						
V _{IH}	HIGH-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	1.2	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		2.0	1.5	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	1.2	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		-	1.5	8.0	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_O = -100 \mu A;$ $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$	V	_{CC} – 0.2	V_{CC}	-	V
		$I_{O} = -6 \text{ mA}; V_{CC} = 2.3 \text{ V}$	V	_{CC} – 0.3	$V_{CC}-0.08$	-	V
		$I_0 = -12 \text{ mA}; V_{CC} = 2.3 \text{ V}$	V	_{CC} – 0.6	V _{CC} - 0.26	-	V
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	V	_{CC} – 0.5	V _{CC} - 0.14	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 3.0 \text{ V}$	V	_{CC} – 0.6	V _{CC} - 0.09	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	V	_{CC} – 1.0	V _{CC} - 0.28	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_O = 100 \mu A;$ $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$		-	GND	0.20	V
		$I_0 = 6 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	0.07	0.40	V
		$I_O = 12 \text{ mA}$; $V_{CC} = 2.3 \text{ V}$		-	0.15	0.70	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$		-	0.14	0.40	V
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	0.27	0.55	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$		-	0.1	5	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		-	0.1	10	μΑ
I _{CC}	supply current	$V_{CC} = 2.3 \text{ V to } 3.6 \text{ V};$ $V_{I} = V_{CC} \text{ or GND; } I_{O} = 0 \text{ A}$		-	0.2	40	μΑ
Δl _{CC}	additional supply current	per data I/O pin; $V_{CC} = 2.3 \text{ V}$ to 3.6 V; $V_{I} = V_{CC} - 0.6 \text{ V}$; $I_{O} = 0 \text{ A}$		-	150	750	μΑ
I _{BHL}	bus hold LOW current	$V_{CC} = 2.3 \text{ V}; V_I = 0.7 \text{ V}$	[2]	45	-	-	μΑ
		$V_{CC} = 3.0 \text{ V}; V_I = 0.8 \text{ V}$	[2]	75	150	-	μΑ
I _{BHH}	bus hold HIGH current	$V_{CC} = 2.3 \text{ V}; V_I = 1.7 \text{ V}$	[2]	-45	-	-	μΑ
		$V_{CC} = 3.0 \text{ V}; V_I = 2.0 \text{ V}$	[2]	-75	-175	-	μΑ
I _{BHLO}	bus hold LOW overdrive current	$V_{CC} = 3.6 \text{ V}$	[2]	500	-	-	μΑ
Івнно	bus hold HIGH overdrive current	$V_{CC} = 3.6 \text{ V}$	[2]	-500	-	-	μΑ
Cı	input capacitance			-	4.0	-	pF
C _{I/O}	input/output capacitance			-	8.0	-	pF

^[1] All typical values are measured at T_{amb} = 25 °C.

^[2] Valid for data inputs of bus hold parts only.

10. Dynamic characteristics

Table 7. Dynamic characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V); test circuit Figure 10.

Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
$T_{amb} = -4$	0 °C to +85 °C						
f _{max}	maximum frequency	see Figure 8					
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	150	333	-	MHz
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	150	340	-	MHz
		V _{CC} = 2.7 V		150	333	-	MHz
t _{pd}	propagation delay	An to Bn; Bn to An; see Figure 6	[4]				
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	1.0	2.8	5.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.0	3.0	4.2	ns
		$V_{CC} = 2.7 \text{ V}$		-	3.0	4.6	ns
		LEAB, LEBA to Bn, An; see Figure 8					
		V_{CC} = 2.3 V to 2.7 V	[2]	1.1	3.5	6.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.3	3.4	4.8	ns
		$V_{CC} = 2.7 \text{ V}$		-	3.6	5.3	ns
		CPAB, CPBA to Bn, An; see Figure 8					
		V_{CC} = 2.3 V to 2.7 V	[2]	1.0	3.3	6.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.4	3.3	4.9	ns
		$V_{CC} = 2.7 \text{ V}$		-	3.4	5.6	ns
t _{en}	enable time	OEBA to An; see Figure 7	[4]				
		V_{CC} = 2.3 V to 2.7 V	[2]	1.3	2.8	6.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.1	2.5	5.0	ns
		$V_{CC} = 2.7 \text{ V}$		-	3.3	6.0	ns
		OEAB to Bn; see Figure 7					
		V_{CC} = 2.3 V to 2.7 V	[2]	1.0	2.5	5.8	ns
		V_{CC} = 3.0 V to 3.6 V	[3]	1.0	2.4	4.6	ns
		$V_{CC} = 2.7 \text{ V}$		-	2.7	5.3	ns
t _{dis}	disable time	OEBA to An; see Figure 7	[4]				
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	1.3	2.5	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.3	3.1	4.2	ns
		V _{CC} = 2.7 V		-	3.3	4.6	ns
		OEAB to Bn; see Figure 7					
		V _{CC} = 2.3 V to 2.7 V	[2]	1.5	2.5	6.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.4	2.9	5.0	ns
		V _{CC} = 2.7 V		-	3.6	5.7	ns

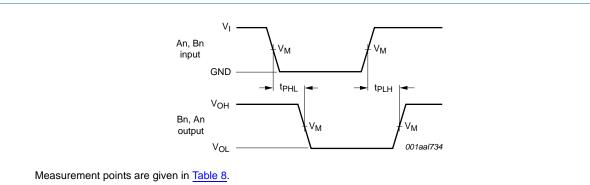
 Table 7.
 Dynamic characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V); test circuit Figure 10.

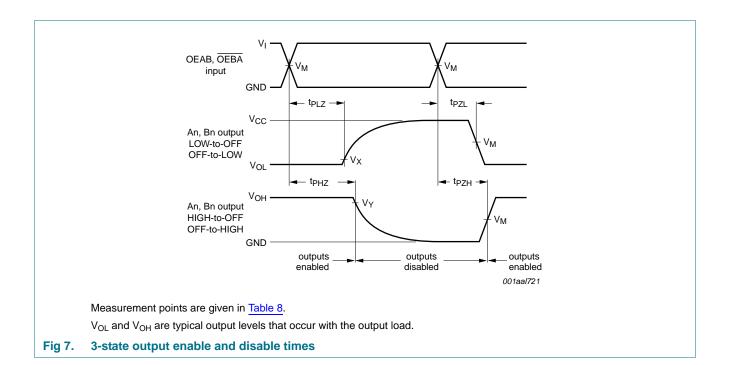
Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
t _W	pulse width	LEAB, LEBA HIGH; see Figure 8					
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	3.3	0.8	-	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	3.3	0.9	-	ns
		$V_{CC} = 2.7 \text{ V}$		3.3	0.7	-	ns
		CPAB, CPBA HIGH or LOW; see Figure 8					
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	3.3	2.0	-	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	3.3	1.1	-	ns
		$V_{CC} = 2.7 \text{ V}$		3.3	1.4	-	ns
t _{su}	set-up time	An, Bn to CPAB, CPBA; see Figure 9					
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	1.7	0.1	-	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.3	-0.3	-	ns
		$V_{CC} = 2.7 \text{ V}$		1.4	-0.1	-	ns
		An, Bn to LEAB, LEBA; see Figure 9					
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	1.1	0.1	-	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.0	0.3	-	ns
		$V_{CC} = 2.7 \text{ V}$		1.0	-0.2	-	ns
t _h	hold time	An, Bn to CPAB, CPBA; see Figure 9					
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	1.7	0.3	-	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[3]	1.3	0.4	-	ns
		$V_{CC} = 2.7 \text{ V}$		1.6	0.3	-	ns
		An, Bn to LEAB, LEBA; see Figure 9					
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	[2]	1.6	0.3	-	ns
		V _{CC} = 3.0 V to 3.6 V	[3]	1.2	0.1	-	ns
		V _{CC} = 2.7 V		1.5	0.1	-	ns
C _{PD}	power dissipation	per buffer; $V_I = GND$ to V_{CC}	<u>[5]</u>				
	capacitance	outputs enabled		-	21	-	pF
		outputs disabled		-	3	-	рF

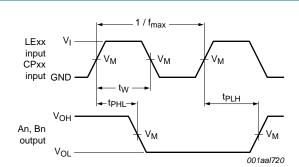
- [1] All typical values are measured at T_{amb} = 25 °C.
- [2] Typical values are measured at V_{CC} = 2.5 V.
- [3] Typical values are measured at V_{CC} = 3.3 V.
- [4] t_{pd} is the same as t_{PLH} and t_{PHL} .
 - t_{en} is the same as t_{PZL} and $t_{\text{PZH}}.$
 - t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 - $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 - f_i = input frequency in MHz;
 - f_o = output frequency in MHz;
 - C_L = output load capacitance in pF;
 - V_{CC} = supply voltage in Volts;
 - N = total load switching outputs;
 - \sum (C_L \times V_{CC}² \times f_o) = sum of outputs.

11. Waveforms



 V_{OL} and V_{OH} are typical output levels that occur with the output load. Fig 6. Propagation delay, data input (An, Bn) to data output (Bn, An)

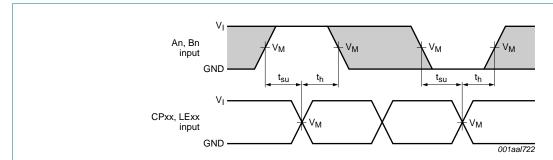




Measurement points are given in Table 8.

 $\ensuremath{V_{OL}}$ and $\ensuremath{V_{OH}}$ are typical output levels that occur with the output load.

Fig 8. Propagation delay, latch enable input (LEAB, LEBA) and clock pulse input (CPAB, CPBA) to data output, and pulse width



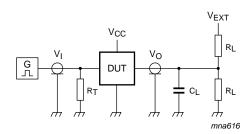
Measurement points are given in Table 8.

Fig 9. Data set-up and hold times (An, Bn inputs to LEAB, LEBA, CPAB and CPBA inputs)

Table 8. Measurement points

Supply voltage	Input		Output				
V _{CC}	VI	V _M	V _M	V _X	V _Y		
2.3 V to 2.7 V and $<$ 2.3 V	V _{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	V _{OH} – 0.15 V		
2.7 V	2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$		
3.0 V to 3.6 V	2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH}-0.3\ V$		

12. Test information



Test data is given in Table 9.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance includes jig and probe capacitance.

 R_T = Termination resistance should be equal to Z_o of pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 10. Load circuit for measuring switching times

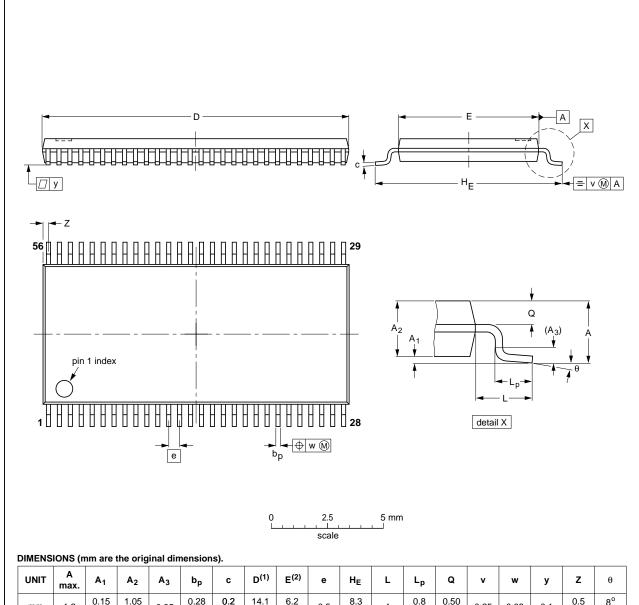
Table 9. Test data

Supply voltage	Input		Load		V_{EXT}		
V _{CC}	VI	t _r , t _f	CL	R _L	t _{PLH} , t _{PHL}	t_{PLZ} , t_{PZL}	t _{PHZ} , t _{PZH}
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	500Ω	open	$2\times V_{CC}$	GND
2.7 V	2.7 V	2.5 ns	50 pF	500Ω	open	$2\times V_{CC}$	GND
3.0 V to 3.6 V	2.7 V	2.5 ns	50 pF	500Ω	open	$2\times V_{CC}$	GND

13. Package outline

TSSOP56: plastic thin shrink small outline package; 56 leads; body width 6.1 mm

SOT364-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	٧	w	у	Z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	14.1 13.9	6.2 6.0	0.5	8.3 7.9	1	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.5 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

	REFER	EUROPEAN	ISSUE DATE			
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
	MO-153				-99-12-27 03-02-19	
	IEC	IEC JEDEC		IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION	

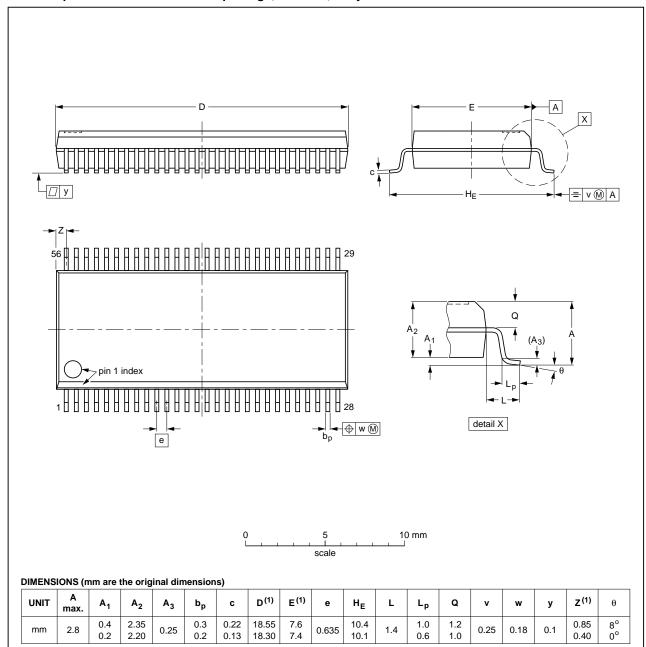
Fig 11. Package outline SOT364-1 (TSSOP56)

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SSOP56: plastic shrink small outline package; 56 leads; body width 7.5 mm

SOT371-1



Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT371-1		MO-118				99-12-27 03-02-18	
						03-02-18	

Fig 12. Package outline SOT371-1 (SSOP56)

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14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
74ALVCH16501 v.5	20120710	Product data sheet	-	-	74ALVCH16501 v.4
Modifications:	Table 8 co	rrected (errata).			
74ALVCH16501 v.4	20111117	Product data sheet	-	-	74ALVCH16501 v.3
Modifications:	 Legal pag 	es updated.			
74ALVCH16501 v.3	20100402	Product data sheet	-	-	74ALVCH16501 v.2
74ALVCH16501 v.2	19980929	Product specification	-	-	74ALVCH16501 v.1
74ALVCH16501 v.1	19980929	Product specification	-	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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18-bit universal bus transceiver; 3-state

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